

Electronic Supplementary Information (ESI)

Controlled synthesis of Co₃O₄ spinel with Co(acac)₃ as precursor

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Table S1: List of solvents and temperature range used for Co₃O₄ preparation

Precursor	Temperature (°C)	Preparation techniques	Solvents	Reference
Co(acac) ₂	230-440	PSE-CVD	EtOH	¹
Co(acac) ₂	490-560	MOCVD	EtOH/chloroform	²
Co ₂ (CO) ₈	600, 650	PE-CVD	1-Hexene	³
Co(hfac) ₂ ·2H ₂ O·tetraglyme	65-180	MOCVD	CH ₂ Cl ₂	⁴
Co(tmhd) ₂	350-500	CVD	-	⁵
	350-540	MOCVD	Monoglyme	⁶
CoCl ₂	300	Spray pyrolysis	Distilled water	⁷⁻⁹
Co(CH ₃ CO ₂) ₂ ·4H ₂ O	600	Sol-gel	2-Methoxyethanol	¹⁰
Co(NO ₃) ₂	400-480	Spray pyrolysis	-	¹¹
Co(acac) ₃	360-540	MOCVD	Toluene	¹²

Note: PSE-CVD: pulsed spray chemical vapor deposition

MOCVD: metal organic vapor deposition

PE-CVD: pulsed evaporation

acac: acetylacetone (2, 4-pentanedionate)

hfac: hexafluoroacetylacetone (1,1,1,5,5,5-Hexafluoro-2,4-pentanedione)

tmhd: tetramethylheptanedionate (2,2,6,6-tetramethyl-3,5-heptanedionate)

Table S2: Experimental conditions for the preparation of Co₃O₄

Precursor	Co(acac) ₃
Solvent	EtOH; toluene or THF
Concentration of precursor	5 mM
Frequency and opening time	4 Hz, ~2 ms
Evaporation temperature	220 °C
Vaporizer temperature	240 °C
Substrate temperature range	350 °C; 400 °C; 450 °C and 500 °C
System pressure (mbar)	20
N ₂ (SLM)	0.16
O ₂ (SLM)	0.5
Substrates	Glass, silicon, planar or mesh of stainless steel

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Table S3: Physical properties of the solvents

Physicals properties	Ethanol	Toluene	THF
Boiling point (°C) ^a	78.35	110.65	68.85
Density (g ml ⁻¹) ^b	0.790	0.866	0.880
Vapor pressure (bar, at 220 °C)	46.57 ^a	10.53 ^a	27.36 ^c
Δ _{vap} H° (kJ/mol) ^a	42 ± 2	37 ± 3	32.16
Dipole moment (D, 20 °C) ^b	1.69	0.31	1.75
Hydrogen bonding ^b	19.4	2.0	8.0

Note: ^a data is from NIST chemistry webbook;¹³ ^b data is from Koenhen and Smolders;¹⁴ ^c vapor pressure of THF is from Dortmund data bank.¹⁵

Table S4: Comparison with other results

Catalyst	Weight (mg)	Gas composition	Flow rate (ml min ⁻¹)	T ₉₀ ^a (°C)	GHSV ^b (ml g ⁻¹ h ⁻¹)	Reference
Co ₃ O ₄ thin film	12	1% CO/ 10% O ₂ /89% Ar	15	350	75000	This work
Co ₃ O ₄ bulk	50	1% CO/ 8% O ₂ in He	37	350	44400	¹⁶
CeO ₂	100	2% CO/ 2% O ₂ in N ₂	100	374	60000	
Al ₂ O ₃	100	2% CO/ 2% O ₂ in N ₂	100	394	60000	¹⁷
CeAlO ₃	100	2% CO/ 2% O ₂ in N ₂	100	465	60000	
Pt/H ₂ SO ₄ /ZrO ₂	50	3.5% CO/ 4% O ₂ in N ₂	100	290	120000	¹⁸
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Co ₃ O ₄ thin film	12	1% C ₃ H ₆ /10% O ₂ /89% Ar	15	380	75000	This work
Co ₃ O ₄ thin film	12	2% C ₃ H ₆ / 20% O ₂ /78% Ar	15	385	75000	¹⁹
Au/A ₂ O ₃	200	1.5% C ₃ H ₆ / 4% O ₂ in He	75	410	22500	²⁰
Ag/Al ₂ O ₃	50	3% C ₃ H ₆ / 10% O ₂ in N ₂	10	420	12000	²¹
La _{1.7} Sr _{0.3} CuO ₄ S _{0.2}	200	0.1% C ₃ H ₆ / 5% O ₂ in He	100	500	30000	²²

Note: ^a T₉₀ refers to the temperature at which 90% of the fuel is converted; ^b GHSV is gas hourly space velocity.

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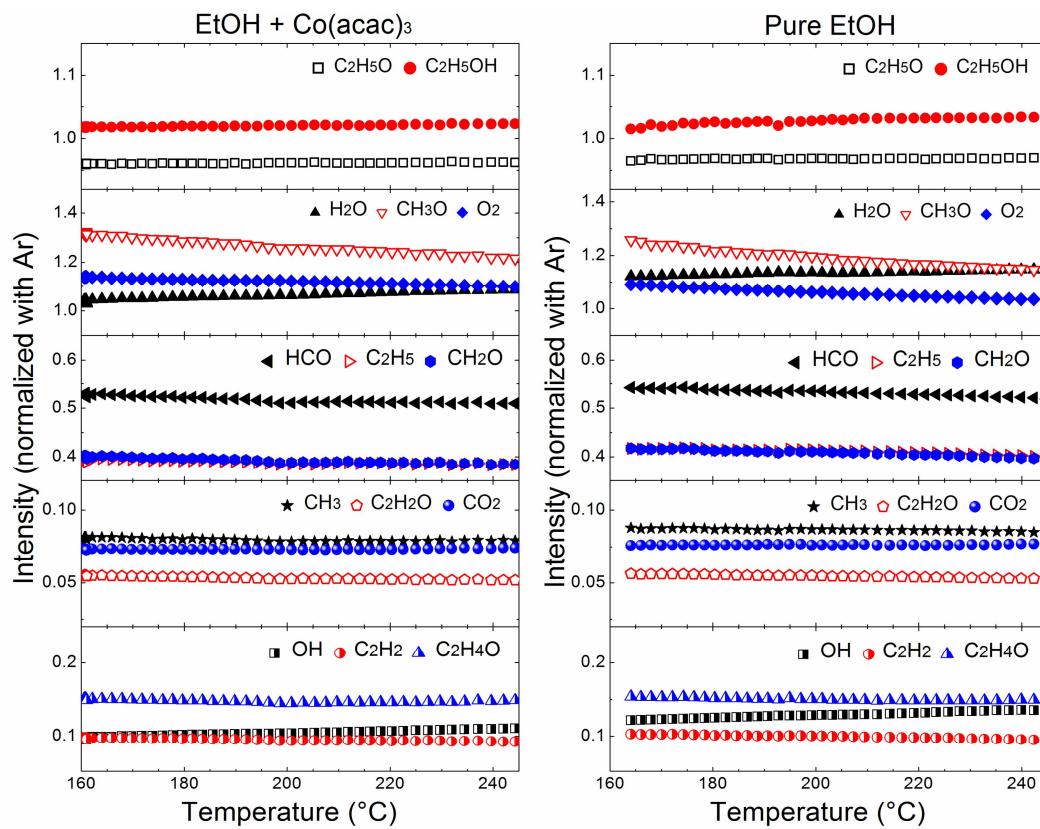


Fig. S1 Gas phase evolution of EtOH with and without Co(acac)₃.

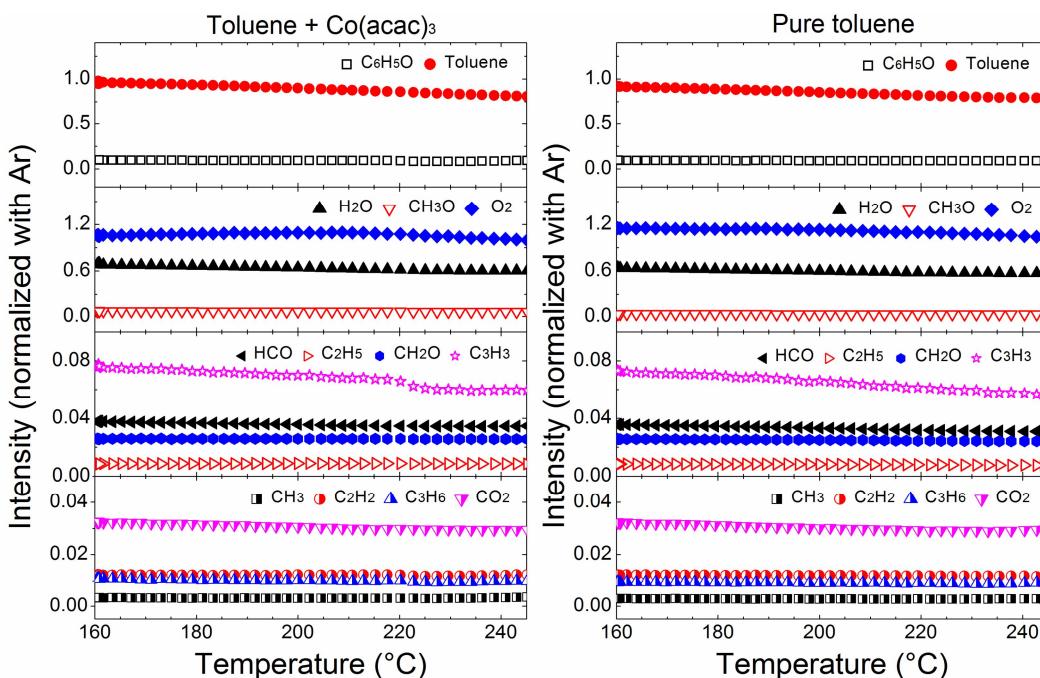


Fig. S2 Gas phase evolution of toluene with and without Co(acac)₃.

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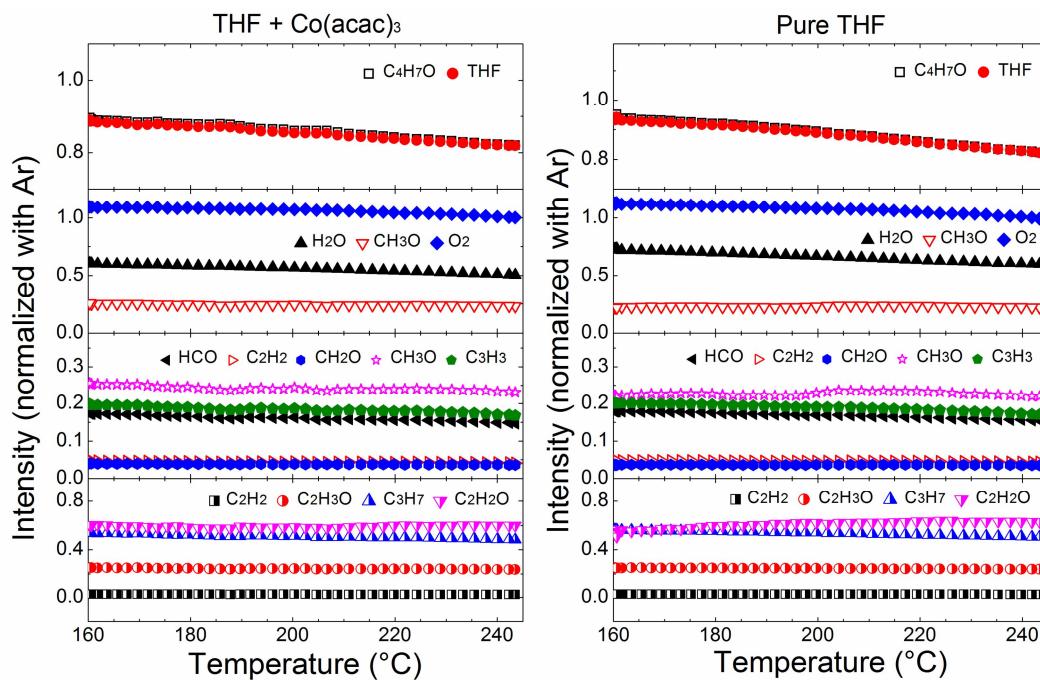


Fig. S3 Gas phase evolution of THF with and without $\text{Co}(\text{acac})_3$.

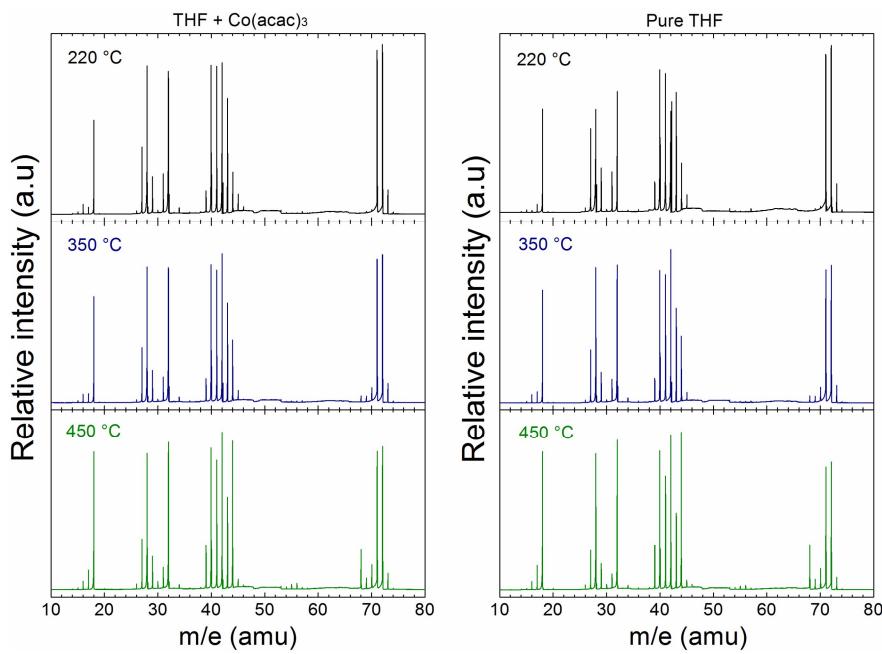


Fig. S4 Gas phase evolution of THF at 220, 350 and 450 $^{\circ}\text{C}$ with and without $\text{Co}(\text{acac})_3$.

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Notes to the figures: Electron impact with an energy of 25 eV was used as the ionization source to perform the experimental investigation. In addition to the fragments generated by the high electron energy, some products, such as C₂H₂ in Fig. S1 and CH₃O in Fig. S3 become detectable. At high temperatures (THF as an example, see Fig. S4), pyrolysis as well as oxidation of the solvent are observed by giving more water (m/e = 18), carbon dioxide (m/e = 44), furan (m/e = 68) and other products, which reveals the occurrence of the gas phase reaction. This is also the case for ethanol and toluene (not shown here). These may affect the kinetics of film growth and morphology.

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